

# P-Channel 12 V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)		
	0.0098 at V <sub>GS</sub> = - 4.5 V	- 23.5			
- 12	0.015 at V <sub>GS</sub> = - 2.5 V	- 15.2	35 nC		
	0.02/ at V <sub>GS</sub> = - 1.8 V	- 10.5			

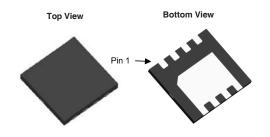
#### **FEATURES**

- DT-Trench Power MOSFET
- Ultra Small DFN3x3 Chipscale Packaging Reduces Footprint Area, Profile (0.62 mm) and On-Resistance Per Footprint Area



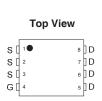


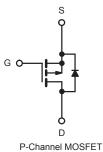
#### DFN 3x3 EP



#### **APPLICATIONS**

- PA Switch
- **Battery Switch**
- Load Switch





<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage		V <sub>DS</sub>	- 12	V		
Gate-Source Voltage		$V_{GS}$	± 8	V		
	T <sub>C</sub> = 25 °C		- 23.5			
Continuous Prain Current (T. = 150 °C)	T <sub>C</sub> = 70 °C	,	- 26.7			
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>A</sub> = 25 °C	I <sub>D</sub>	- 20.7 <sup>b, c</sup>			
	T <sub>A</sub> = 70 °C		- 08.7 <sup>b, c</sup>	Α		
Pulsed Drain Current	I <sub>DM</sub>	- 105				
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	I-	- 16.7			
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	I <sub>S</sub>	- 3.5 <sup>b, c</sup>			
	T <sub>C</sub> = 25 °C		37			
Maximum Dawar Dissination	T <sub>C</sub> = 70 °C	P <sub>D</sub>	26	W		
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	r <sub>D</sub>	2.9 <sup>b, c</sup>	VV		
	T <sub>A</sub> = 70 °C		1.96 <sup>b, c</sup>			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C		
Package Reflow Conditions <sup>d</sup>	IR/Convection		260	C		

- a. Based on T<sub>C</sub> = 25 °C.
  b. Surface mounted on 1" x 1" FR4 board.
- d. Refer to IPC/JEDEC (J-STD-020), no manual or hand soldering.
- e. In this document, any reference to the Case represents the body of the DFN2X2 device and Foot is the bump.



THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient <sup>a, b</sup>		R <sub>thJA</sub>	31	42	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	13	16	C/VV	

#### Notes:

- a. Surface mounted on 1" x 1" FR4 board.b. Maximum under steady state conditions is 72 °C/W.

<b>SPECIFICATIONS</b> (T <sub>.I</sub> = 25 °C, unless otherwise noted)							
Parameter	Symbol	ymbol Test Conditions		Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250  \text{OA}$	- 12			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = - 250 òA		- 13.3		mV/°C	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	1D = - 230 0A		2.4		] """/ C	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -250 \text{ oA}$	- 0.75		- 0.9	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 0/ V			- 100	nA	
Zero Gate Voltage Drain Current	1	V <sub>DS</sub> = -8 V, V <sub>GS</sub> = 0 V	-1		2.0		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -8 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C			- 10	òΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le 5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20			А	
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 1 A		0.0/87	0.012	Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 1 A		0.015	0.018		
		V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 1 A		0.020	0.024		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = -4 V, I <sub>D</sub> = -1 A		8.3		S	
Dynamic <sup>b</sup>				•		•	
Input Capacitance	C <sub>iss</sub>			2220			
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -6 V, V <sub>GS</sub> = 0 V, f = 1 MHz		865		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			555		1	
Total Gate Charge	Q <sub>q</sub>	$V_{DS} = -6 \text{ V}, V_{GS} = -5 \text{ V}, I_{D} = -1 \text{ A}$		38	57		
Total Gate Charge	₹g			35	53	nC	
Gate-Source Charge	$Q_{gs}$	$V_{DS}$ = -6 V, $V_{GS}$ = -4.5 V, $I_{D}$ = -1 A		7.3			
Gate-Drain Charge	$Q_{gd}$			5.9		1	
Gate Resistance	R <sub>g</sub>	$V_{GS} = -0.1 \text{ V, f} = 1 \text{ MHz}$		28		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			14	21		
Rise Time	t <sub>r</sub>	$V_{DD} = -6 \text{ V}, R_L = 4 \Omega$		25	40	ne	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ - 1 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 6 $\Omega$		380	570	ns ns	
Fall Time	t <sub>f</sub>			240	360		



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<b>SPECIFICATIONS</b> T <sub>J</sub> = 25 °C, unless otherwise noted						
Parameter	rameter Symbol Test Conditions		Min.	Тур.	Max.	Unit
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 30.5	Α
Pulse Diode Forward Current	I <sub>SM</sub>				- 105	^
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 1 A, V <sub>GS</sub> = 0 V		- 0.65	- 1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>			311	467	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = - 1 A, dl/dt = 100 A/òs, T <sub>.I</sub> = 25 °C		1.136	1.705	òC
Reverse Recovery Fall Time	t <sub>a</sub>	1 = - 1 A, and = 100 A/05, 1 J = 25 0		116		ns
Reverse Recovery Rise Time	t <sub>b</sub>			195		115

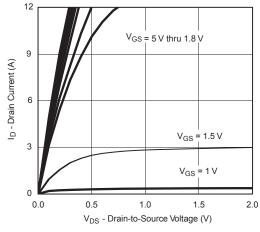
#### Notes:

- a. Pulse test; pulse width  $\leq$  300 òs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

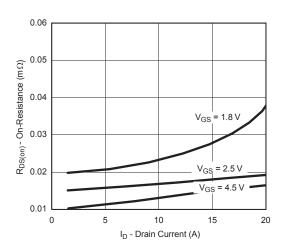
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



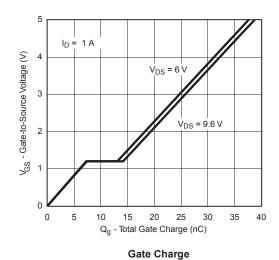
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



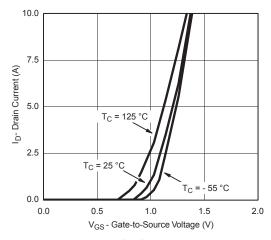
## **Output Characteristics**



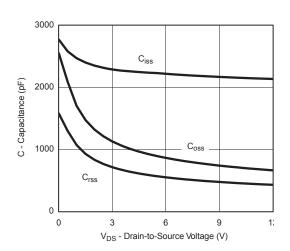
On-Resistance vs. Drain Current and Gate Voltage



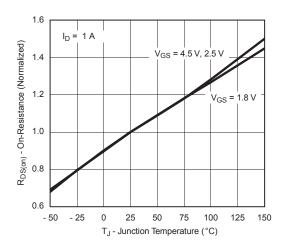
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**Transfer Characteristics** 



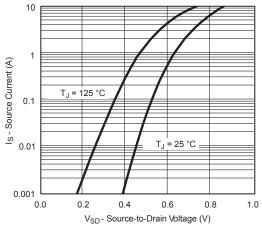
Capacitance



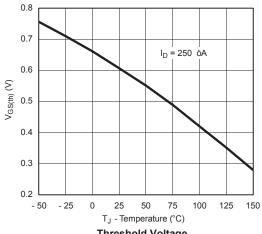
On-Resistance vs. Junction Temperature



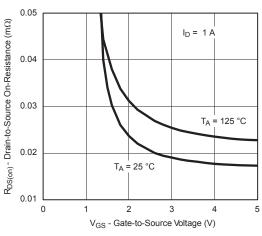
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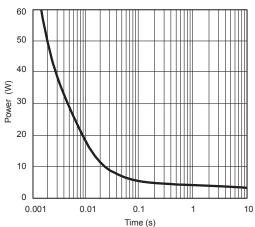
#### Source-Drain Diode Forward Voltage



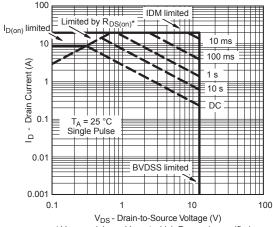
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



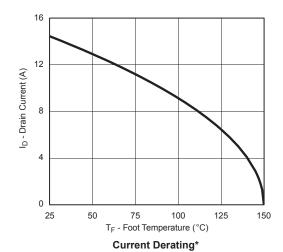
Single Pulse Power, Junction-to-Ambient

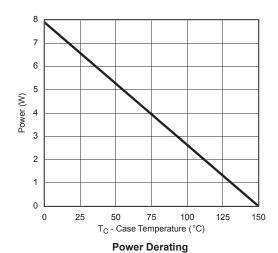


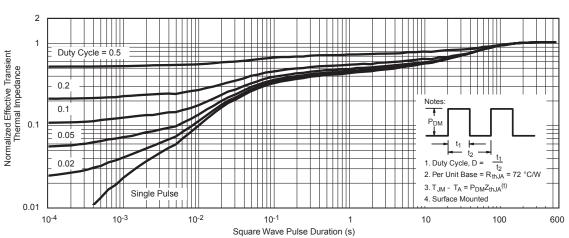
\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified Safe Operating Area, Junction-to-Ambient

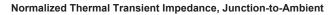


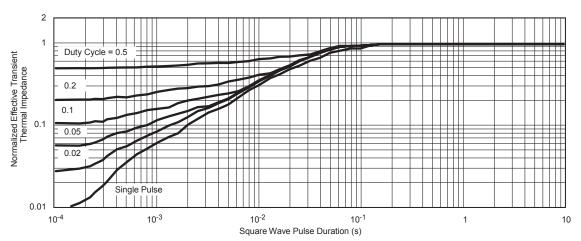
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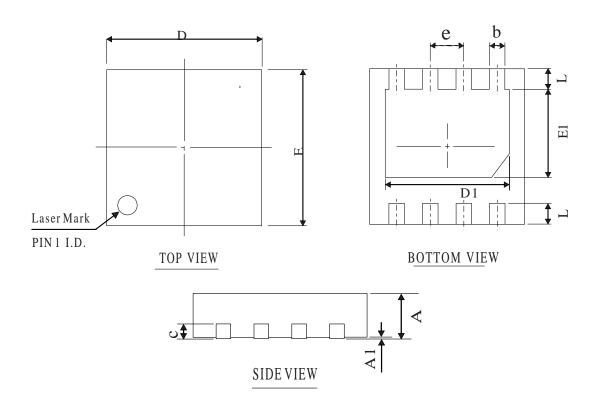






Normalized Thermal Transient Impedance, Junction-to-Foot

# DFN3\*3-8L PACKAGE OUTLINE



## **COMMON DIMENSIONS** (UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	0. 60	0.75	0. 90
A1	0. 00	0.02	0. 08
b	0. 20	0.30	0.45
D	2. 85	3.00	3. 15
E	2. 85	3.00	3. 15
D1	2. 10	2.40	2. 70
E1	1.50	1.70	2.00
L	0. 20	0.40	0.60
С	0. 203 REF		
e	0. 65 BSC		

### OTHER DIMENSIONS

A	0. 50	0.55	0.60
A	0.40	0.45	0.50



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